

N- and P-Channel 30 V (D-S) MOSFET

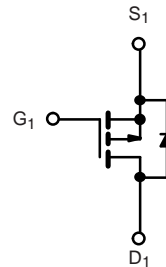
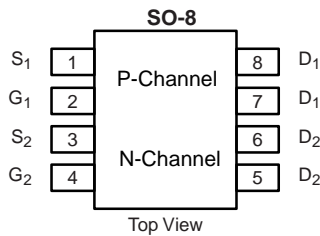
PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
N-Channel	30	0.018 at V _{GS} = 10 V	7.0	2.75
		0.024 at V _{GS} = 4.5 V	5.2	
P-Channel	- 30	0.036 at V _{GS} = - 10 V	- 6.9	4.1
		0.040 at V _{GS} = - 4.5 V	- 5.4	

FEATURES

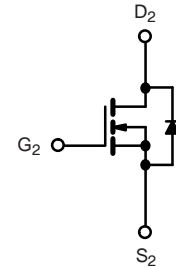
- DT-Trench Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT



P-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V _{DS}	30	- 30	V
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	7.0	- 6.9	A
	T _C = 70 °C	4.9	- 4.4	
	T _A = 25 °C	5.9 ^{b, c}	- 5.4 ^{b, c}	
	T _A = 70 °C	3.9 ^{b, c}	- 3.7 ^{b, c}	
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	21	- 21	A
Source-Drain Current Diode Current	T _C = 25 °C	2.3	- 2.3	
	T _A = 25 °C	1.5 ^{b, c}	- 1.5 ^{b, c}	
Pulsed Source-Drain Current	I _{SM}	24	- 12	mJ
Single Pulse Avalanche Current	I _{AS}	7	8	
Single Pulse Avalanche Energy	E _{AS}	2.5	3.2	W
Maximum Power Dissipation	T _C = 25 °C	2.78	2.78	
	T _C = 70 °C	1.78	1.78	
	T _A = 25 °C	1.78 ^{b, c}	1.78 ^{b, c}	
	T _A = 70 °C	1.14 ^{b, c}	1.14 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	N-Channel		P-Channel		Unit	
		Typ.	Max.	Typ.	Max.		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	57	70	57	70	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	37	45	37	45	

Notes:

- a. Based on T_C = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under steady state conditions is 120 °C/W (N-Channel) and 110 °C/W (P-Channel).

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)								
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	N-Ch	30			V	
		$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-30				
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		33		mV/ $^\circ\text{C}$	
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		-33			
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		-5.8			
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		4.5			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	1.0		3.0	V	
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-1.0		-3.0		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	N-Ch			100	nA	
			P-Ch			-100		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	μA	
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1		
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	N-Ch			5		
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	P-Ch			-5		
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	N-Ch	20			A	
		$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	P-Ch	-12				
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.5\text{ A}$	N-Ch		0.011	0.018	Ω	
		$V_{GS} = -10\text{ V}, I_D = -3.5\text{ A}$	P-Ch		0.023	0.036		
		$V_{GS} = 4.5\text{ V}, I_D = 2.8\text{ A}$	N-Ch		0.012	0.024		
		$V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$	P-Ch		0.03	0.04		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 2.5\text{ A}$	N-Ch		7		S	
		$V_{DS} = -15\text{ V}, I_D = -3.5\text{ A}$	P-Ch		7			
Dynamic^a								
Input Capacitance	C_{iss}	N-Channel $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		305		pF	
			P-Ch		340			
Output Capacitance	C_{oss}		N-Ch		65			
			P-Ch		67			
Reverse Transfer Capacitance	C_{rss}	P-Channel $V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		29			
			P-Ch		51			
Total Gate Charge	Q_g		$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$	N-Ch		6	9	nC
				P-Ch		7.8	12	
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 2.5\text{ A}$	N-Ch		2.75	4.5		
			P-Ch		4.1	6.2		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 2.5\text{ A}$	N-Ch		1.3			
P-Ch			1.3					
Gate-Drain Charge	Q_{gd}	P-Channel $V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$	N-Ch		0.9			
			P-Ch		1.8			
Gate Resistance	R_g		$f = 1\text{ MHz}$	N-Ch	0.6	3.1	6.2	Ω
				P-Ch	2.0	10	20	

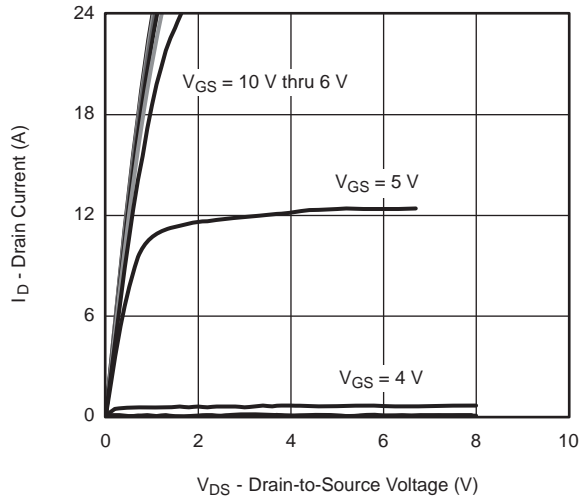
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Dynamic^a							
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$ P-Channel $V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$	N-Ch		7	11	ns
			P-Ch		5.5	10	
Rise Time	t_r		N-Ch		12	18	
			P-Ch		13	25	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		14	25	
			P-Ch		17	30	
Fall Time	t_f		N-Ch		6	10	
			P-Ch		7.7	15	
Turn-On Delay Time	$t_{d(on)}$	N-Ch		16	30		
		P-Ch		40	60		
Rise Time	t_r	N-Ch		16	30		
		P-Ch		40	60		
Turn-Off Delay Time	$t_{d(off)}$	N-Ch		9	18		
		P-Ch		20	40		
Fall Time	t_f	N-Ch		9	18		
		P-Ch		17	30		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	N-Ch			4.3	A
			P-Ch			-4.3	
Pulse Diode Forward Current ^a	I_{SM}		N-Ch			21	
			P-Ch			-21	
Body Diode Voltage	V_{SD}	$I_S = 1.25\text{ A}$ $I_S = -0.75\text{ A}$	N-Ch		0.8	1.2	V
			P-Ch		-0.8	-1.2	
Body Diode Reverse Recovery Time	t_{rr}	N-Channel $I_F = 1.25\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ P-Channel $I_F = -2.5\text{ A}, di/dt = -100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$	N-Ch		14	21	ns
P-Ch			17	30			
Body Diode Reverse Recovery Charge	Q_{rr}		N-Ch		6	10	nC
			P-Ch		11	20	
Reverse Recovery Fall Time	t_a	N-Ch		9		ns	
		P-Ch		12			
Reverse Recovery Rise Time	t_b	N-Ch		5			
		P-Ch		5			

Notes:

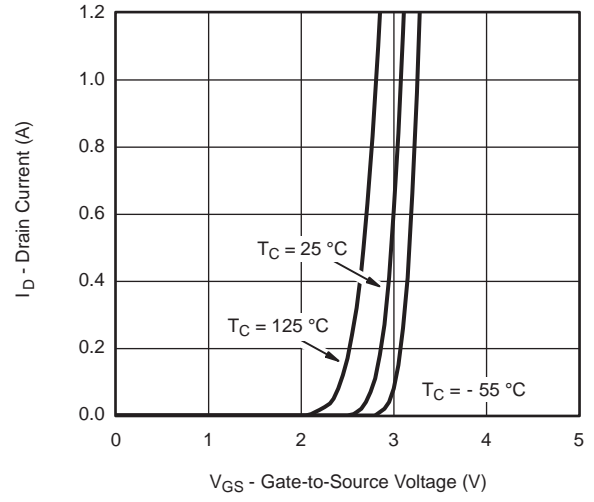
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

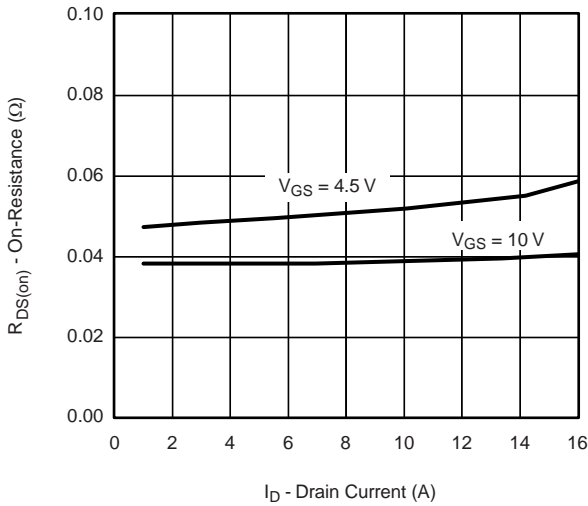
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



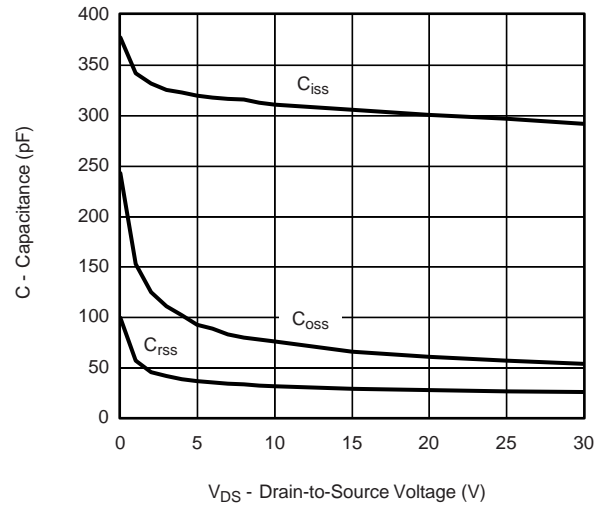
Output Characteristics



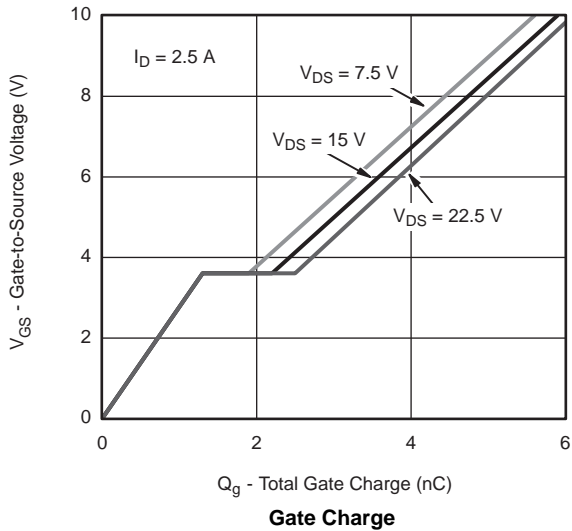
Transfer Characteristics



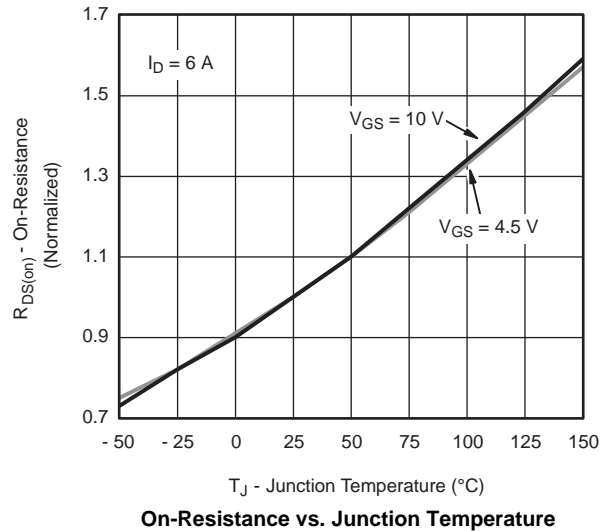
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

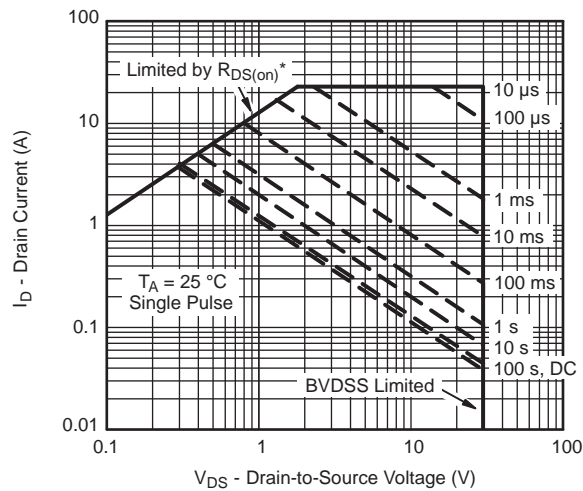
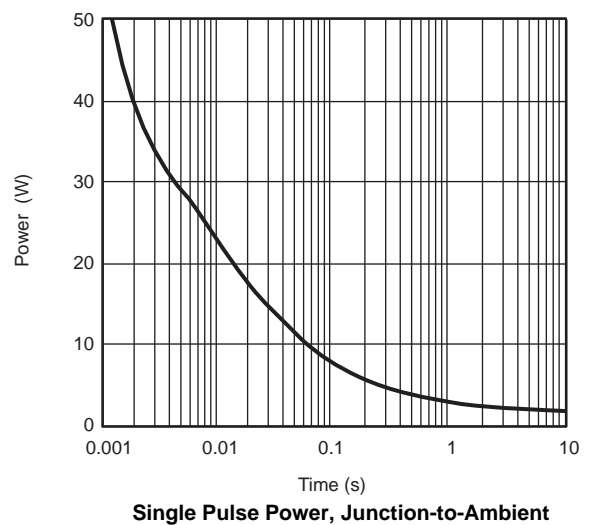
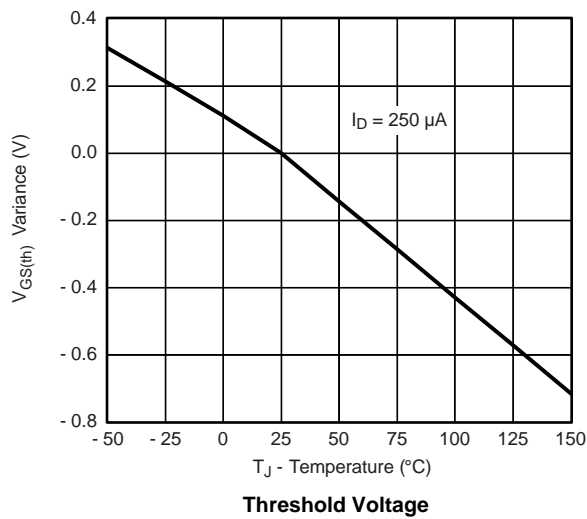
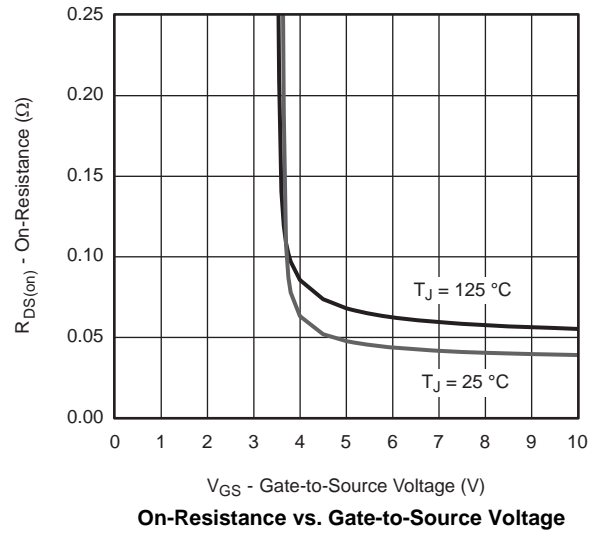
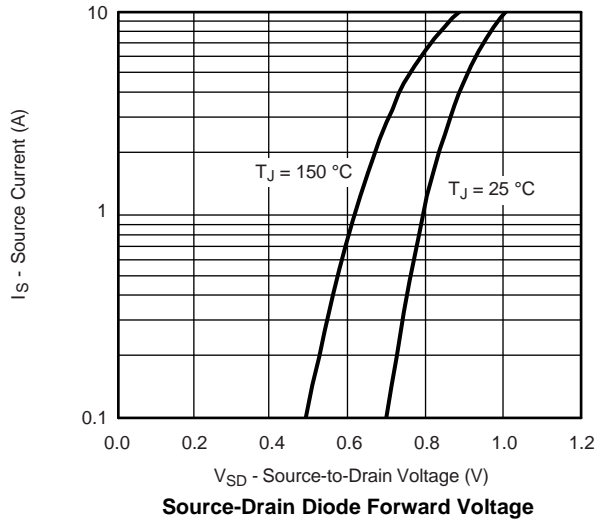


Gate Charge



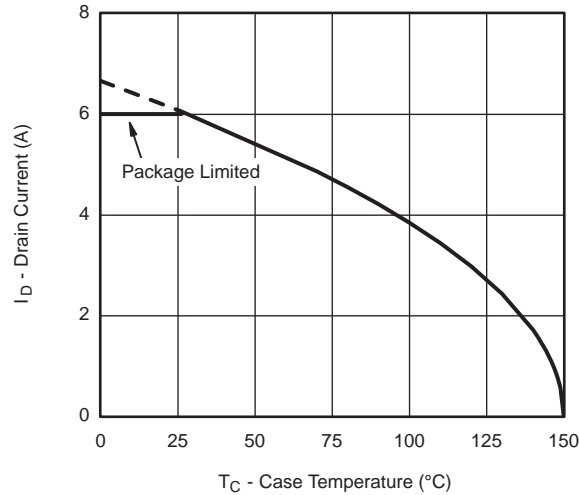
On-Resistance vs. Junction Temperature

N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

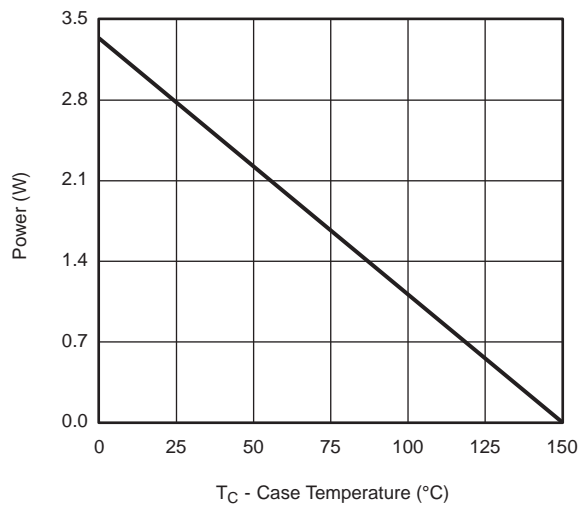


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

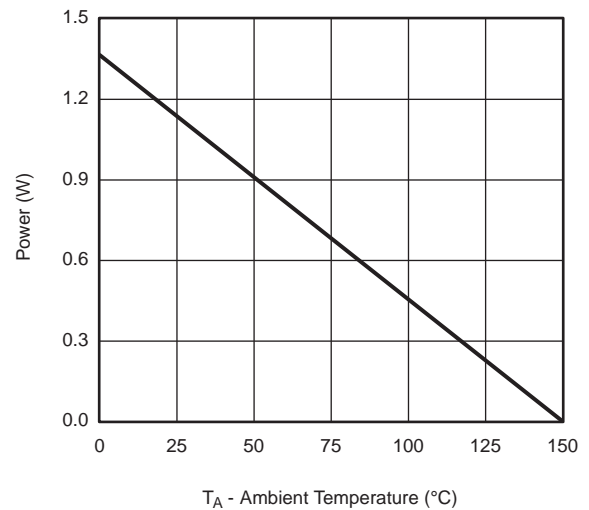
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



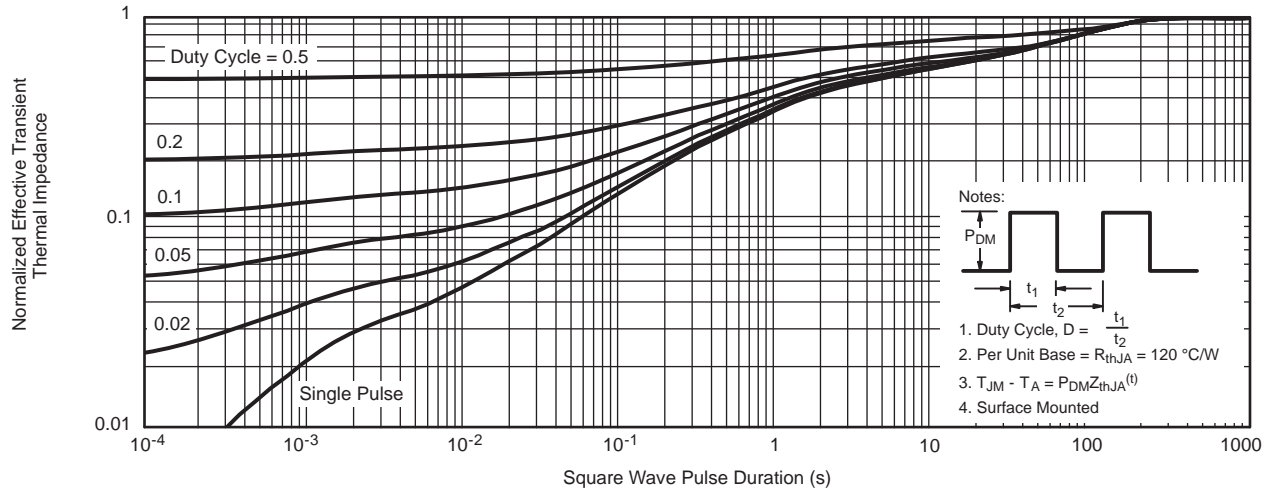
Power Derating, Junction-to-Foot



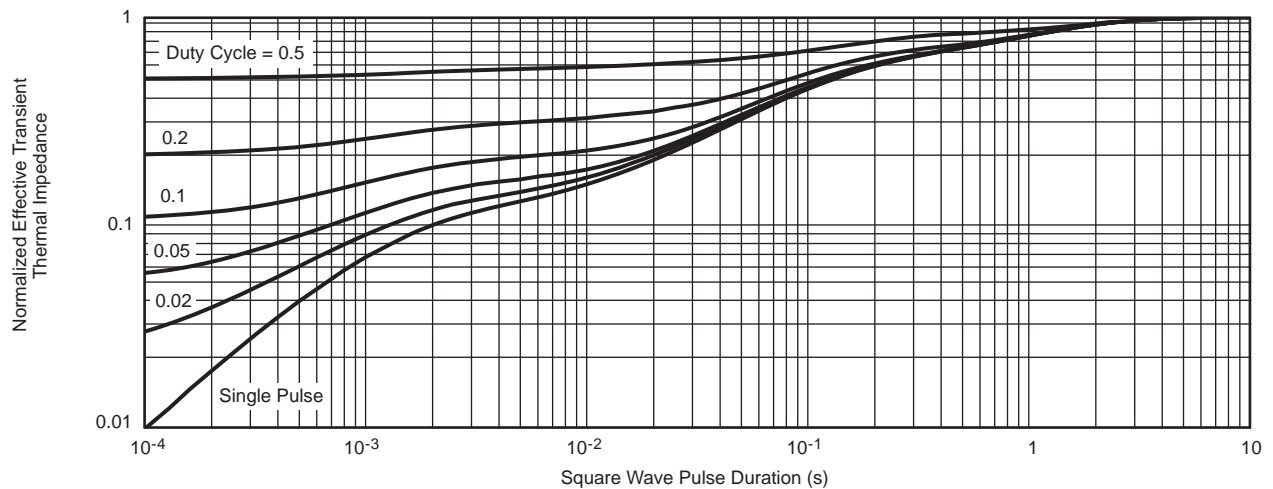
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

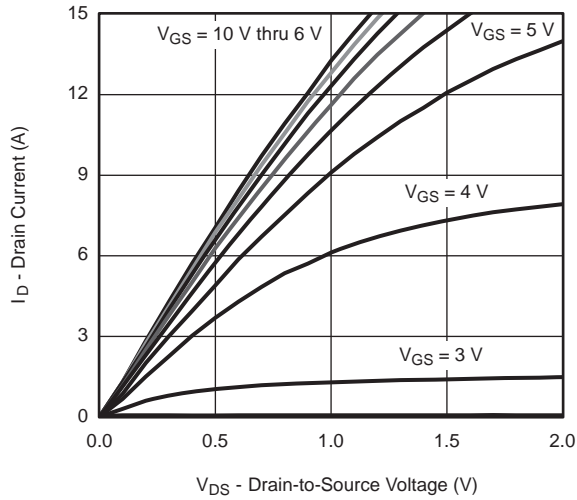


Normalized Thermal Transient Impedance, Junction-to-Ambient

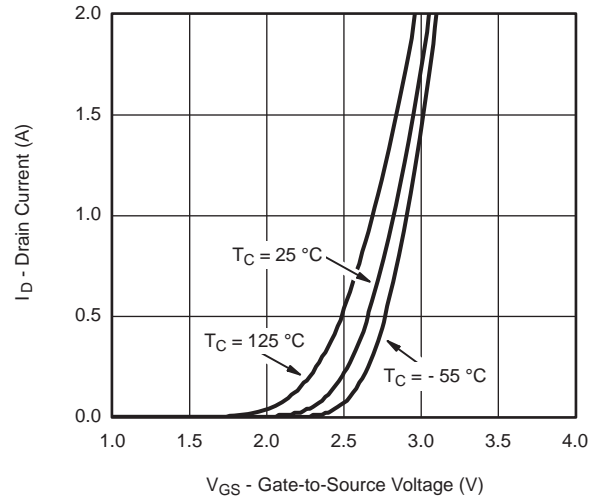


Normalized Thermal Transient Impedance, Junction-to-Foot

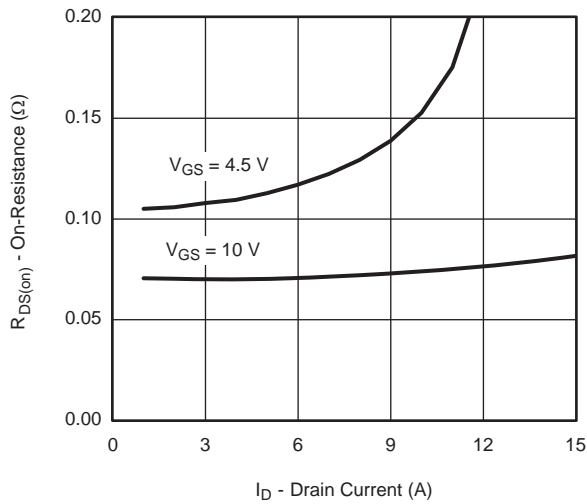
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



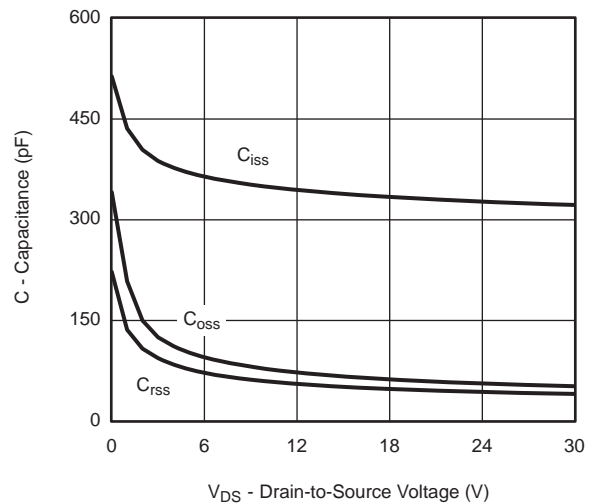
Output Characteristics



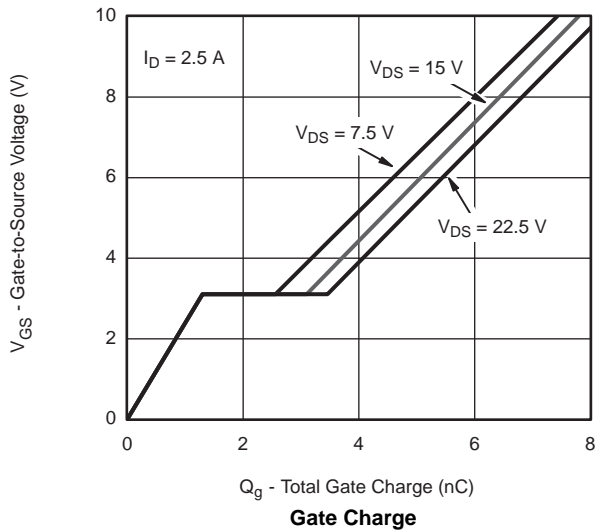
Transfer Characteristics



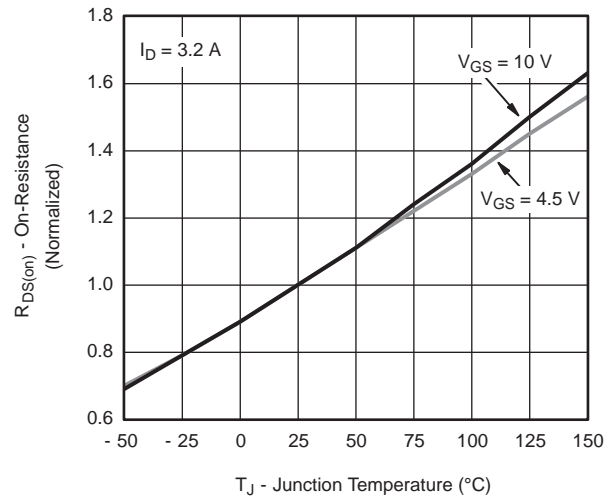
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

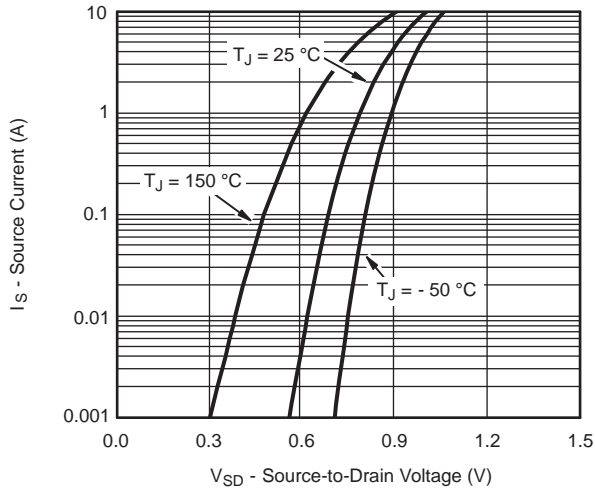


Gate Charge

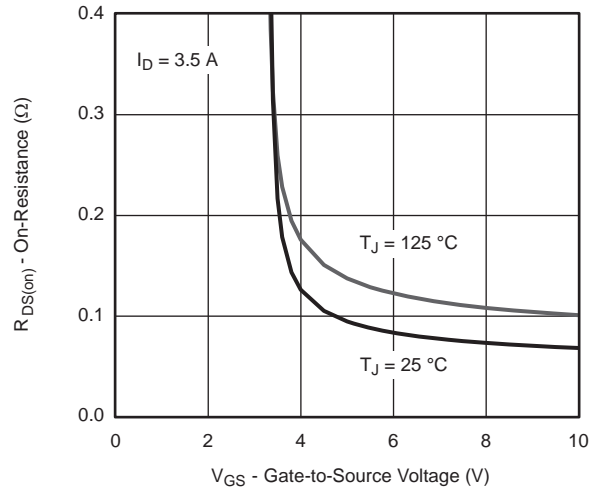


On-Resistance vs. Junction Temperature

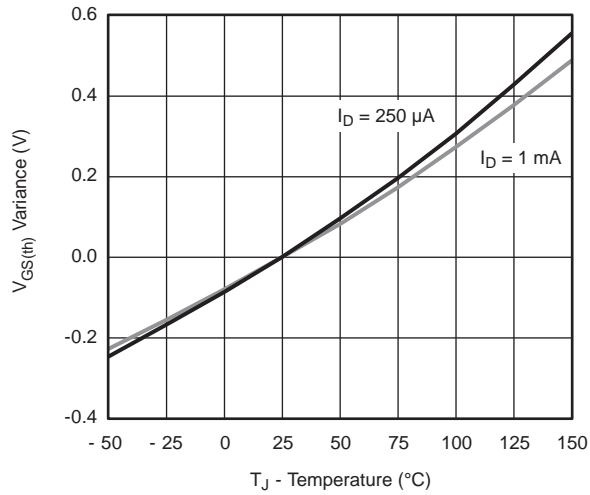
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



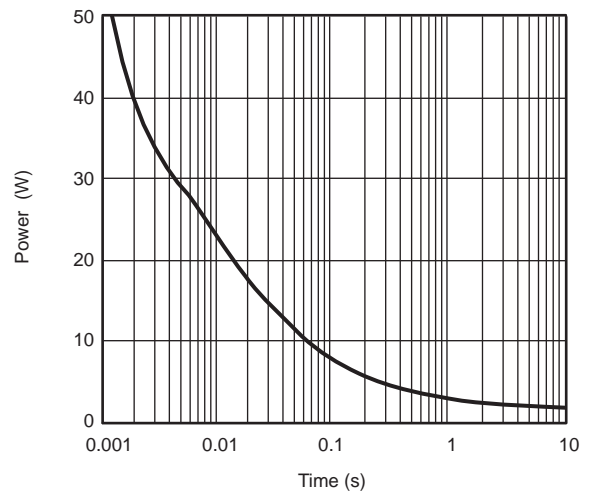
Source-Drain Diode Forward Voltage



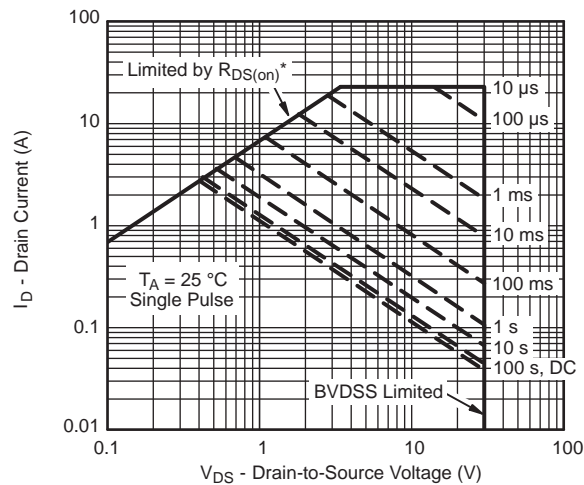
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



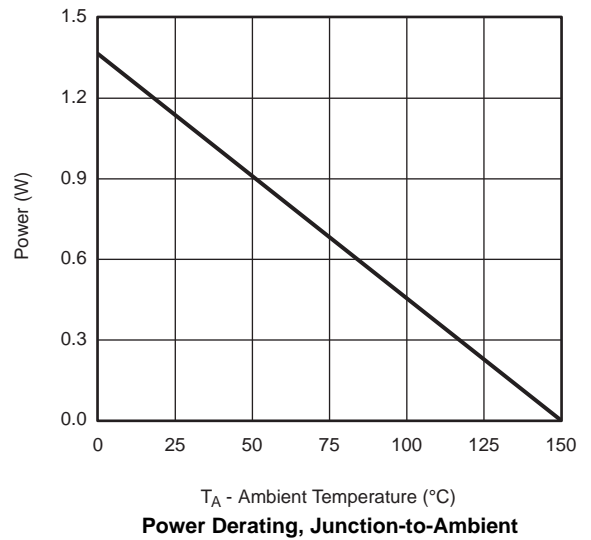
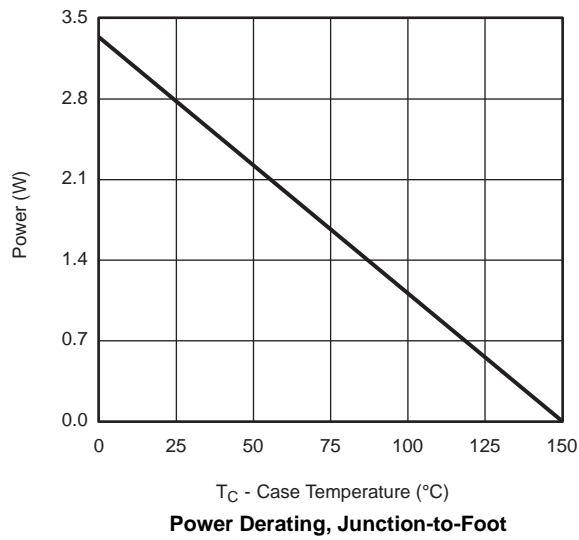
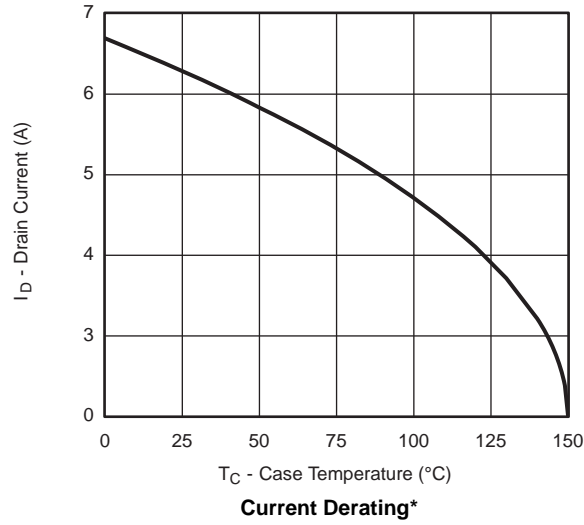
Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

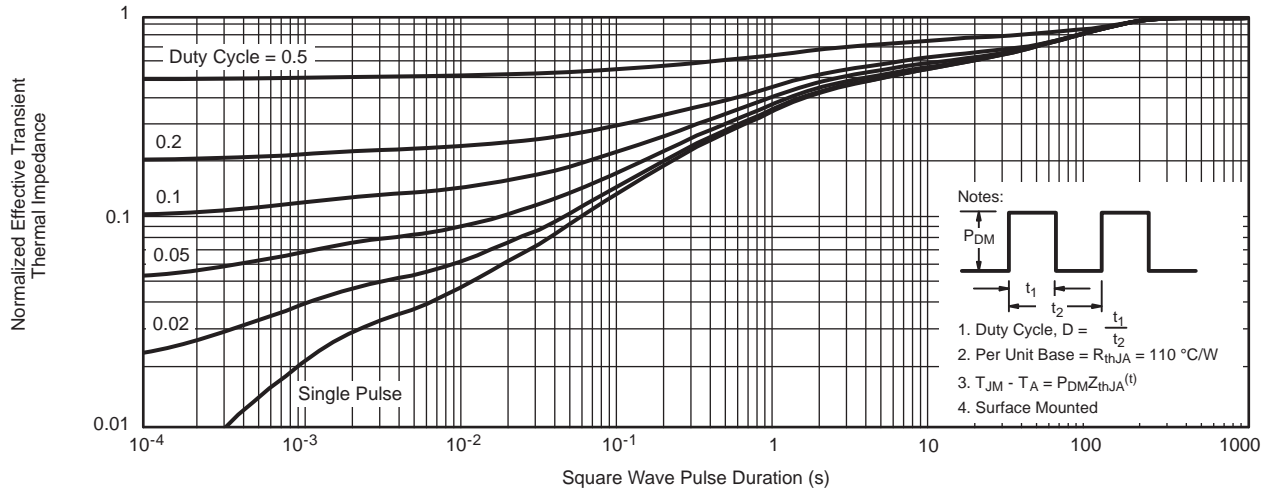
Safe Operating Area, Junction-to-Ambient

P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

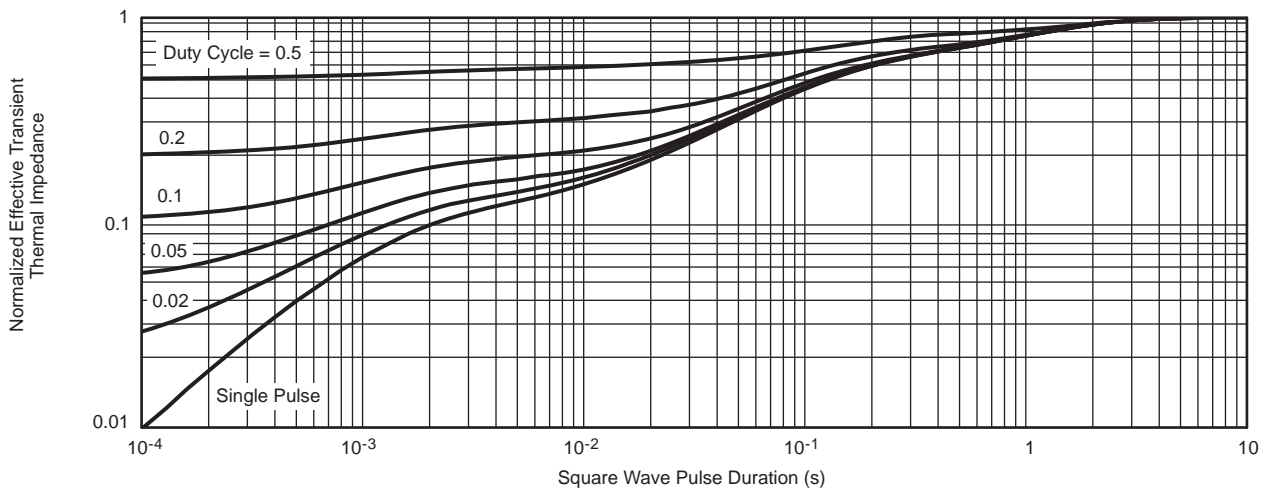


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P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

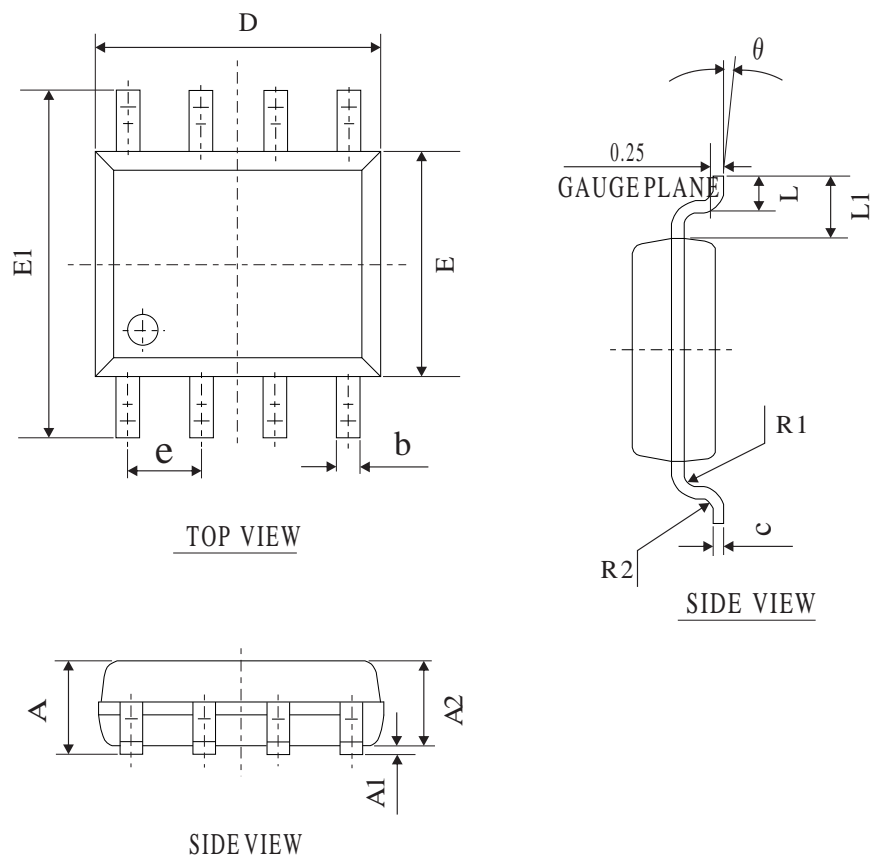


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

SOP-8 PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
A	1.30	1.60	1.85
A1	0.03	0.15	0.28
A2	1.20	1.45	1.70
b	0.26	0.40	0.54
C	0.132	0.203	0.273
D	4.50	4.90	5.30
E	3.50	3.00	4.30
E1	5.50	6.00	6.50
L	0.30	0.70	1.10
θ	2°	4°	6°
L1	1.04REF		
e	1.27BSC		
R1	0.07TYP		
R2	0.07TYP		

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